

GDE C200 PLASMA ETCH SYSTEM

System Overview

GDE C200 is an ICP etch system for dielectric etch and compound semiconductors, designed with ultra-high density plasma sources for higher etch rates. Configuration options include: single, dual or triple process modules

Substrate Size:	100 mm, 125 mm, 150 mm, 200 mm
Applications compounds:	SiC, SiN, BSG, SiO ₂ , Al ₂ O ₃ , & GaN
Technology Markets:	Advanced Packaging, Power IC, Optical Communication Devices

Processes

- SiC back hole etch
- SiC terminal etch
- SiC MOSFET trench etch
- Other glass materials etch
- Planar Lightwave Circuit etch

Production Advantages

- Provides secondary ionization for higher plasma density
- Excellent performance in etching GaN, SiC, SiN, SiO₂, Al₂O₃ and other materials
- Wide process window—easy to integrate with related processes
- Chamber design optimizes maintainability & uptime
- High conductance pumping system
- Excellent particle control



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